

Applications

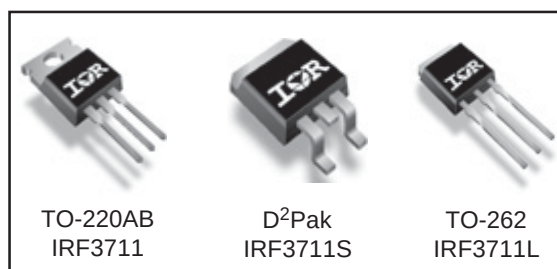
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Server Processor Power Synchronous FET
- Optimized for Synchronous Buck Converters Including Capacitive Induced Turn-on Immunity

Benefits

- Ultra-Low Gate Impedance
- Very Low RDS(on) at 4.5V V_{GS}
- Fully Characterized Avalanche Voltage and Current

HEXFET® Power MOSFET

V _{DSS}	R _{DS(on)} max	I _D
20V	6.0mΩ	110A ^⑥



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-to-Source Voltage	± 20	V
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	110 ^⑥	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	69	
I _{DM}	Pulsed Drain Current ^①	440	
P _D @ T _C = 25°C	Maximum Power Dissipation	120	W
P _D @ T _A = 25°C	Maximum Power Dissipation ^⑤	3.1	W
	Linear Derating Factor	0.96	W/°C
T _J , T _{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case ^⑦	—	1.04	°C/W
R _{θCS}	Case-to-Sink, Flat, Greased Surface ^④	0.50	—	
R _{θJA}	Junction-to-Ambient ^④ ^⑦	—	62	
R _{θJA}	Junction-to-Ambient (PCB mount) ^⑤ ^⑦	—	40	

Notes ^① through ^⑦ are on page 11

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.022	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	4.7	6.0	$m\Omega$	$V_{GS} = 10V, I_D = 15A$ ③ $V_{GS} = 4.5V, I_D = 12A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 16V, V_{GS} = 0V$
		—	—	100		$V_{DS} = 16V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -16V$

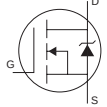
Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	53	—	—	S	$V_{DS} = 16V, I_D = 30A$
Q_g	Total Gate Charge	—	29	44	nC	$I_D = 15A$
Q_{gs}	Gate-to-Source Charge	—	7.3	—		$V_{DS} = 10V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	8.9	—		$V_{GS} = 4.5V$
Q_{oss}	Output Gate Charge	—	33	—		$V_{GS} = 0V, V_{DS} = 10V$
R_g	Gate Resistance	0.3	—	2.5	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	12	—	ns	$V_{DD} = 10V$
t_r	Rise Time	—	220	—		$I_D = 30A$
$t_{d(off)}$	Turn-Off Delay Time	—	17	—		$R_G = 1.8\Omega$
t_f	Fall Time	—	12	—		$V_{GS} = 4.5V$ ③
C_{iss}	Input Capacitance	—	2980	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	1770	—		$V_{DS} = 10V$
C_{rss}	Reverse Transfer Capacitance	—	280	—		$f = 1.0MHz$

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	460	mJ
I_{AR}	Avalanche Current①	—	30	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	110⑥	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	440		
V_{SD}	Diode Forward Voltage	—	0.88	1.3	V	$T_J = 25^\circ\text{C}, I_S = 30A, V_{GS} = 0V$ ③ $T_J = 125^\circ\text{C}, I_S = 30A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	50	75	ns	$T_J = 25^\circ\text{C}, I_F = 16A, V_R = 10V$
Q_{rr}	Reverse Recovery Charge	—	61	92	nC	$di/dt = 100A/\mu s$ ③
t_{rr}	Reverse Recovery Time	—	48	72	ns	$T_J = 125^\circ\text{C}, I_F = 16A, V_R = 10V$
Q_{rr}	Reverse Recovery Charge	—	65	98	nC	$di/dt = 100A/\mu s$ ③

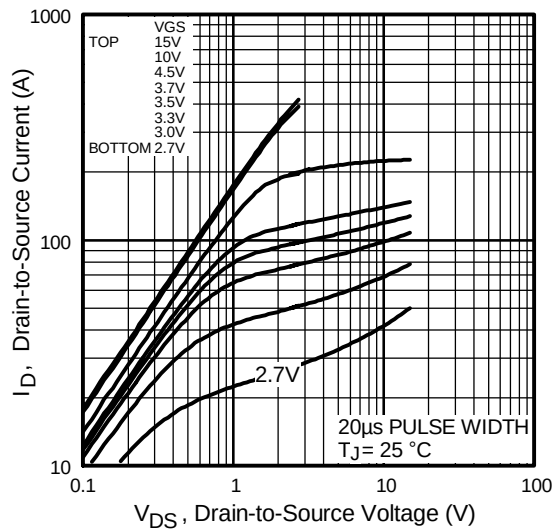


Fig 1. Typical Output Characteristics

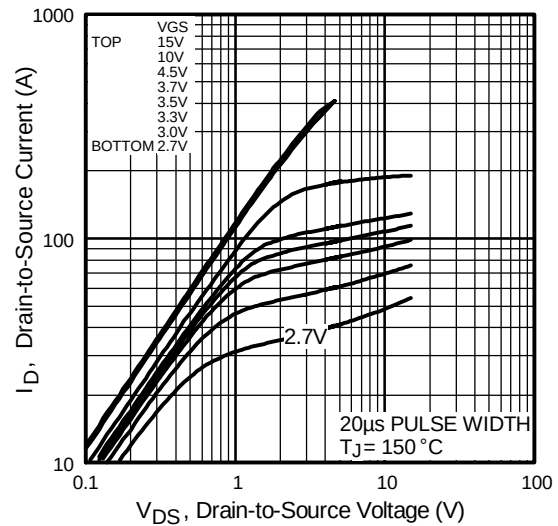


Fig 2. Typical Output Characteristics

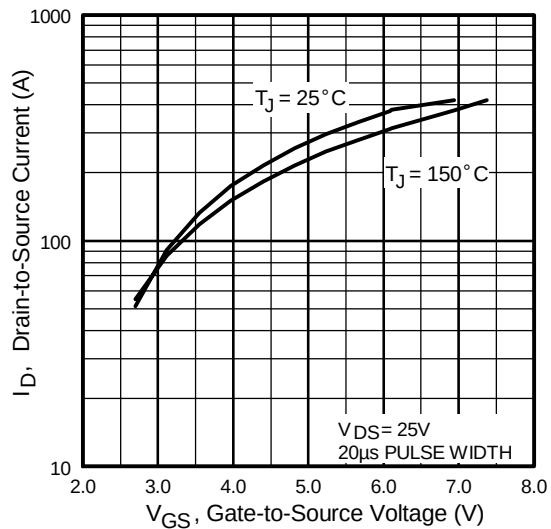


Fig 3. Typical Transfer Characteristics

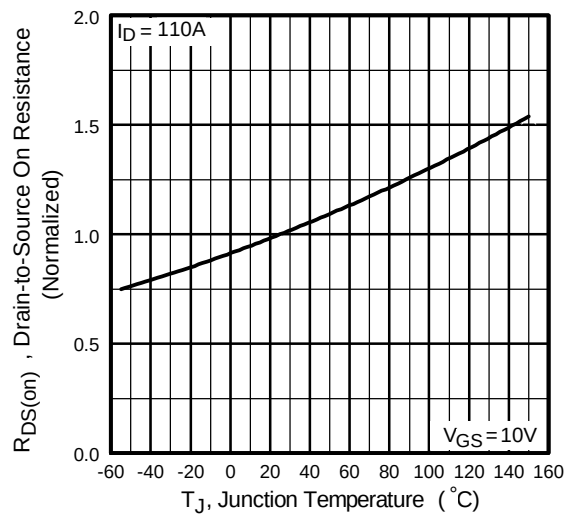


Fig 4. Normalized On-Resistance
Vs. Temperature

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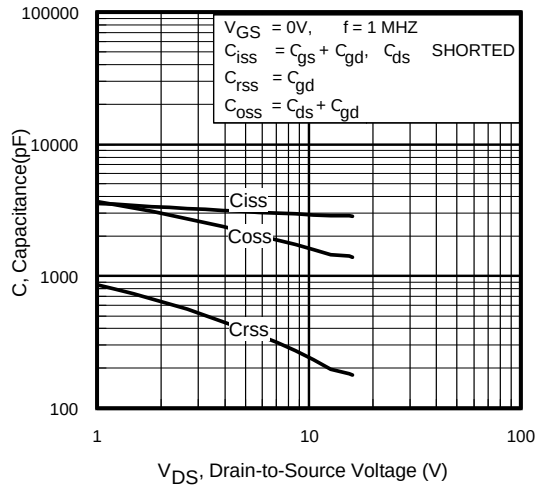


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

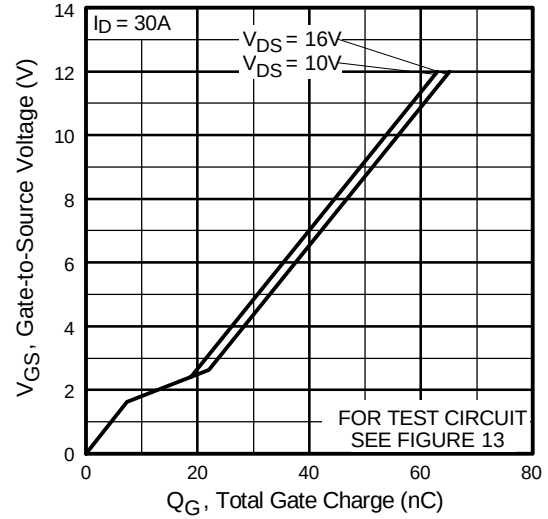


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

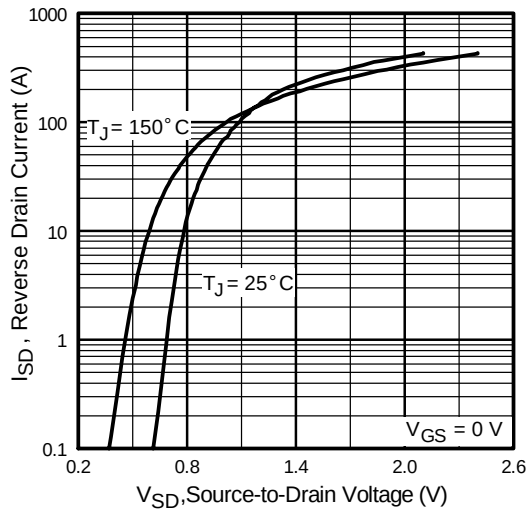


Fig 7. Typical Source-Drain Diode Forward Voltage

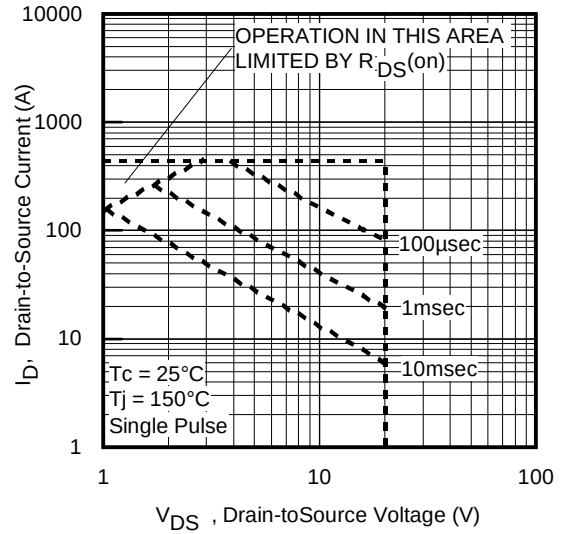


Fig 8. Maximum Safe Operating Area

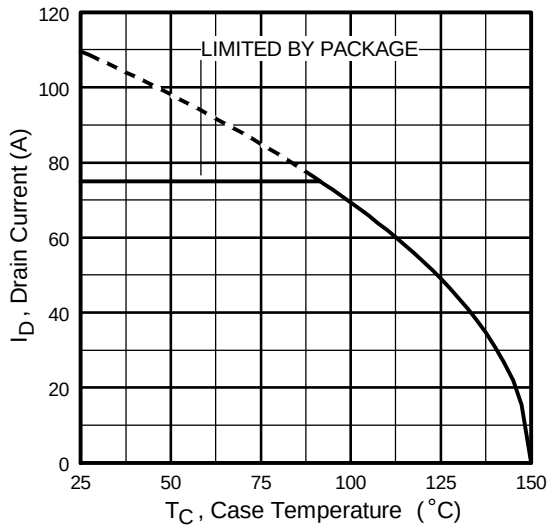


Fig 9. Maximum Drain Current Vs. Case Temperature

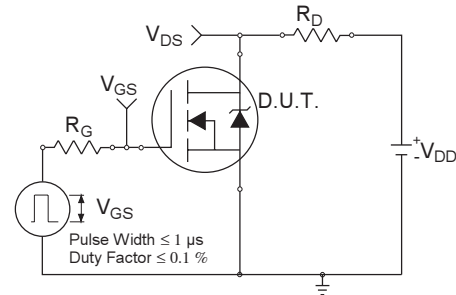


Fig 10a. Switching Time Test Circuit

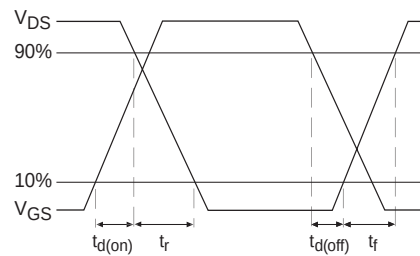


Fig 10b. Switching Time Waveforms

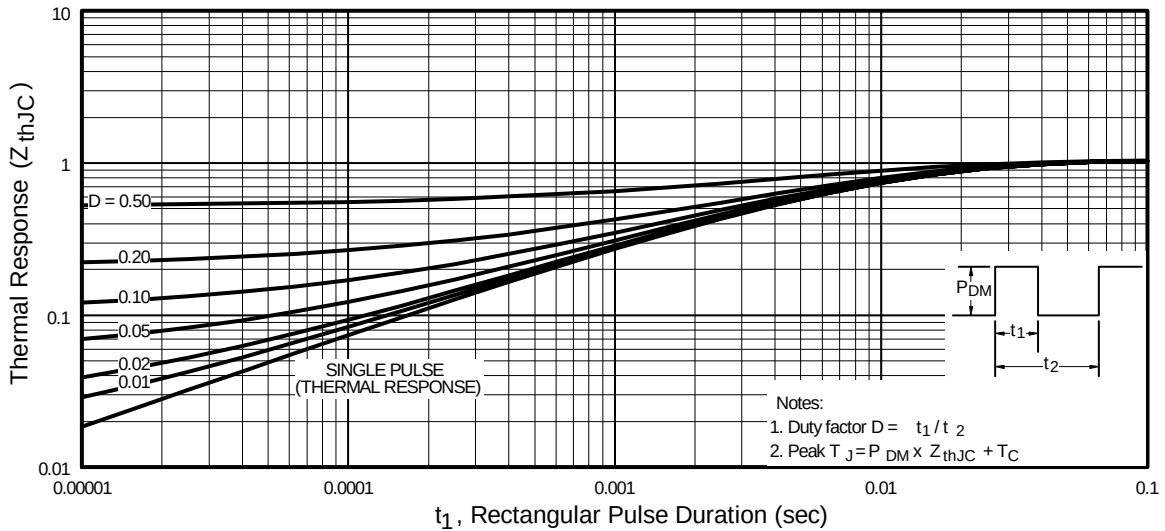


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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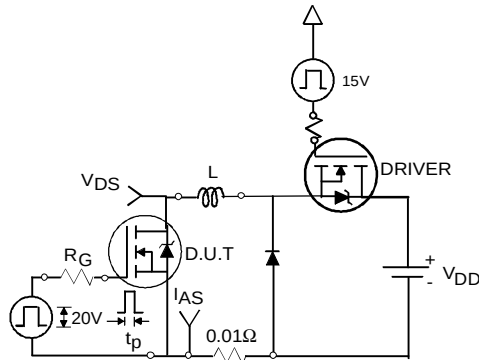


Fig 12a. Unclamped Inductive Test Circuit

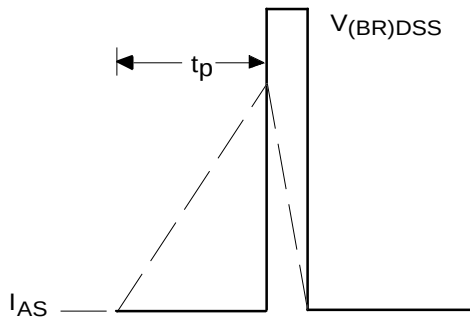


Fig 12b. Unclamped Inductive Waveforms

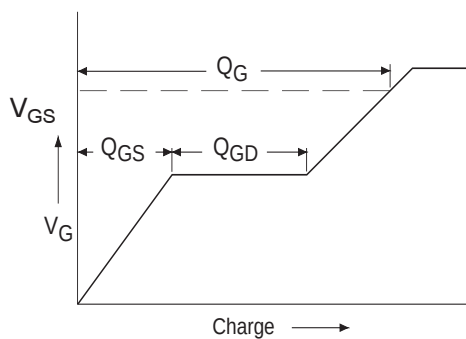


Fig 13a. Basic Gate Charge Waveform

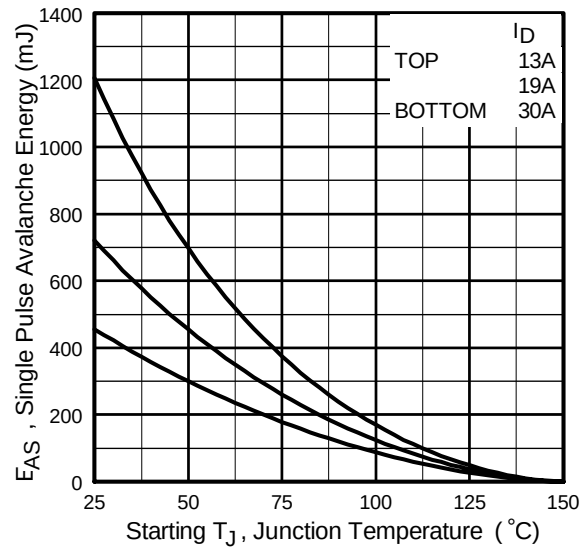


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

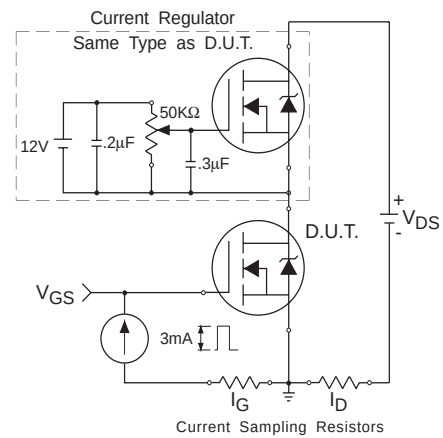
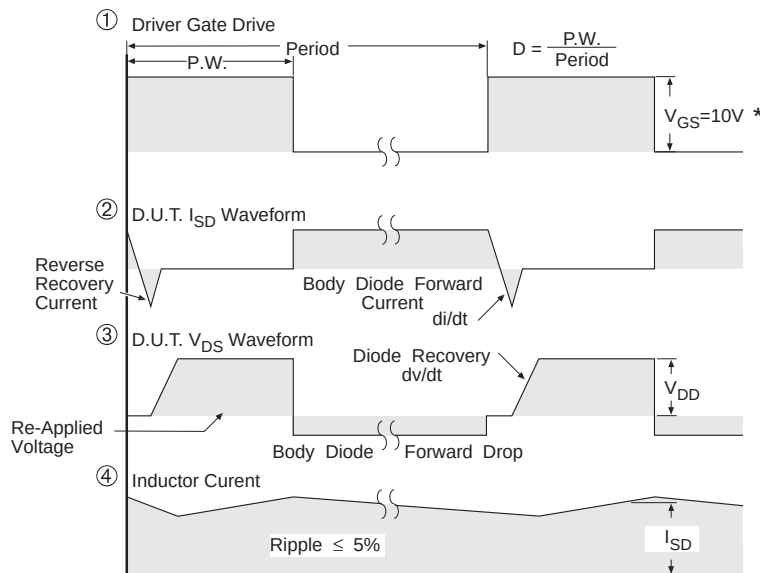
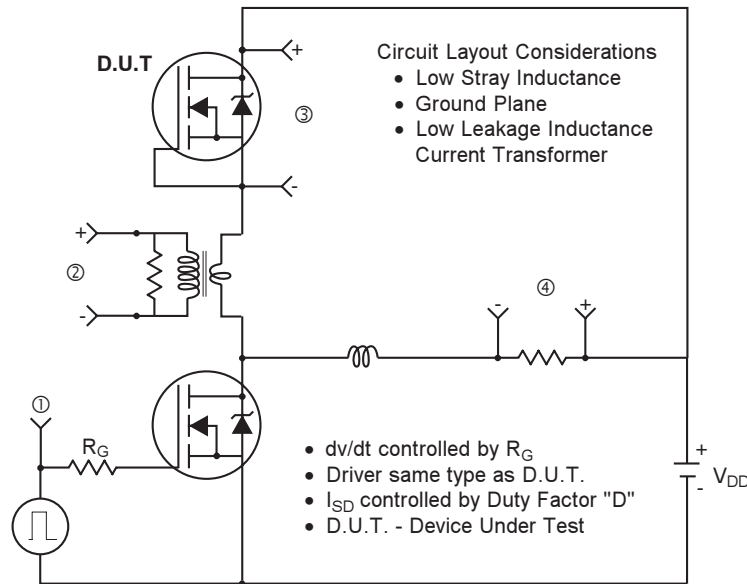


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFET® Power MOSFETs

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Dimensions are shown in millimeters (inches)



- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
2 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
3 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
4 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH
5 SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE
6 MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
7 DIMENSION b1 & c1 APPLY TO BASE METAL ONLY.
8 CONTROLLING DIMENSION: INCHES.
9 THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E.H1,D2 & E1
10 DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING
11 AND SINGULATION IRREGULARITIES ARE ALLOWED.

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

DIODES

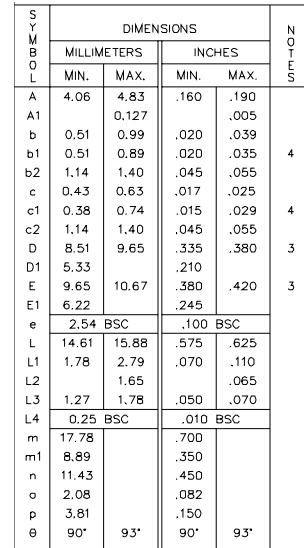
- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-220AB Part Marking Information

Note: "P" in assembly line position indicates "Lead-Free"



Dimensions are shown in millimeters (inches)



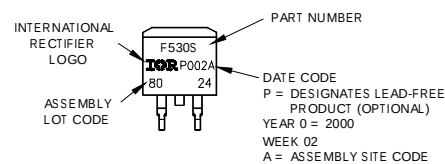
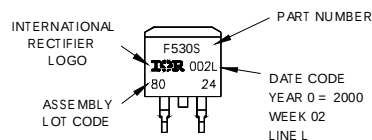
<u>HEXFET</u>	<u>IGBTs, CoPACK</u>	<u>DIODES</u>
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

* PART DEPENDENT.

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line
position indicates "Lead-Free"

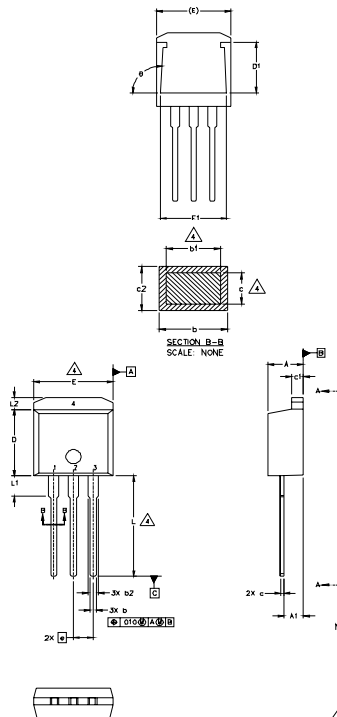


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TO-262 Package Outline

Dimensions are shown in millimeters (inches)



S Y M B O L	DIMENSIONS				N O T E S
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.38	0.63	.015	.025	
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT

- 1 - GATE
- 2 - COLLECTOR
- 3 - EMITTER

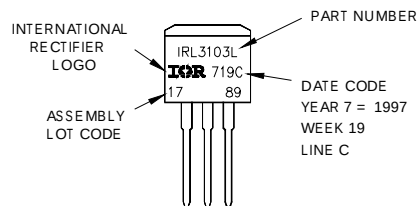
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
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4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

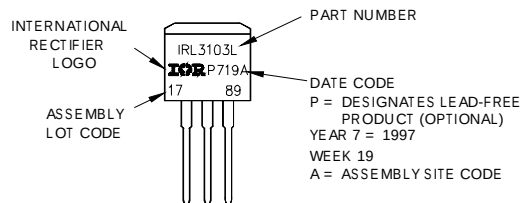
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line
position indicates "Lead-Free"

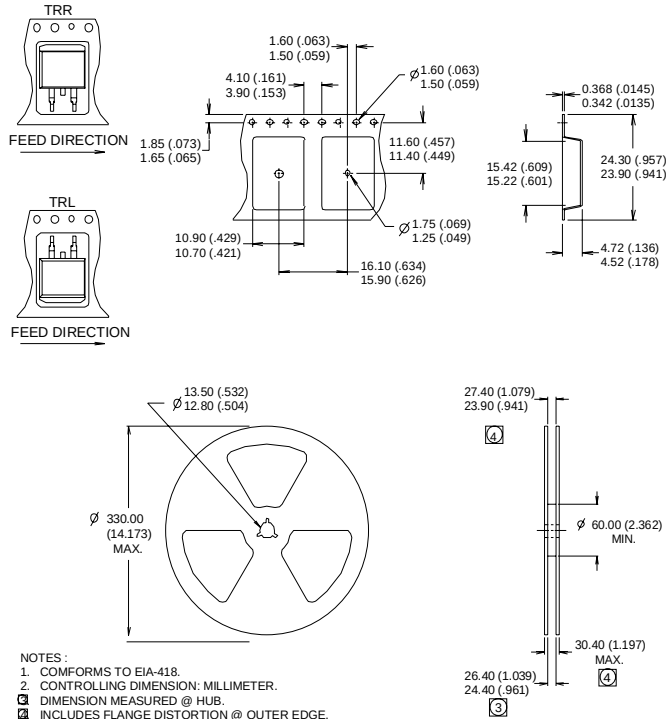


OR



D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 1.0\text{mH}$
 $R_G = 25\Omega$, $I_{AS} = 30\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ This is only applied to TO-220AB package
- ⑤ This is applied to D²Pak, when mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.
- ⑦ R_θ is measured at T_J approximately 90°C

Data and specifications subject to change without notice.
This product has been designed and qualified for the industrial market.
Qualification Standards can be found on IR's Web site.

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>

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